(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
18 October 2012 (18.10.2012)

WIPO | PCT

(10) International Publication Number
WO 2012/141908 A1

(51) International Patent Classification:
H01L 23/00 (2006.01)

(21) International Application Number:
PCT/US2012/031122

(22) International Filing Date:
29 March 2012 (29.03.2012)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
61/474,415 12 April 2011 (12.04.2011) US

(71) Applicant *(for all designated States except US)*: **ASIA UNION ELECTRONIC CHEMICAL COPORATION**; No. 31, Chien-Yeh Road, Ta-Liao Hsian 831, Kaohsiung County, Taiwan (TW).

(72) Inventors; and

(75) Inventors/Applicants *(for US only)*: **DOVE, Curtis** [US/US]; 1703 Tierra Berienda, Pueblo, CO 81008 (US). **SINGH, Baljit** [US/US]; 4184 Asimuth Circle, Union City, CA 94587 (US). **TESNADO, Eduard, Gil Paran** [US/US]; 314 Michell Court, Livermore, CA 94551 (US). **BALOOCH, Mehdi** [US/US]; 551 Colusa Avenue, Berkeley, CA 94707 (US).

(74) Agent: **HEY, David, A.**; Linde LLC, 575 Mountain Ave., Murray Hill, NJ 07974 (US).

(81) Designated States *(unless otherwise indicated, for every kind of national protection available)*: AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PE, PG, PH, PL, PT, QA, RO, RS, RU, RW, SC, SD, SE, SG, SK, SL, SM, ST, SV, SY, TH, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

(84) Designated States *(unless otherwise indicated, for every kind of regional protection available)*: ARIPO (BW, GH, GM, KE, LR, LS, MW, MZ, NA, RW, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AL, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MK, MT, NL, NO, PL, PT, RO, RS, SE, SI, SK,

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(54) Title: LOW TEMPERATURE DEPOSITION OF SILICON OXIDE FILMS

(57) Abstract: Deposition of silicon oxide films at low temperature by using wet chemistry techniques. The wet chemistry solution may be a mixture of sodium hypochloride (NaOCl), tetra methyl ammonium hydroxide (TMAH) and hydrated silicate, such as silicic acid. The resulting silicon oxide films provide excellent anti-reflective coatings for solar cells and the like.

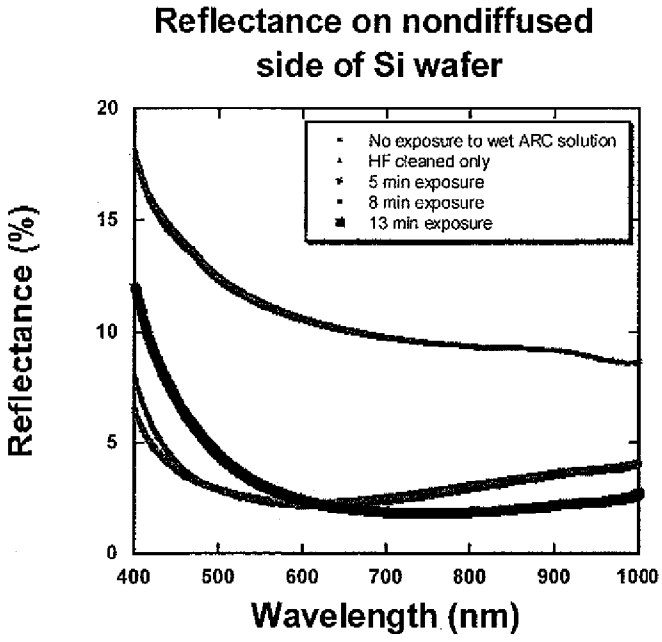


FIG. 1

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SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:

— *with international search report (Art. 21(3))*